CLAIMS

1. A photoresist or semiconductor manufacturing residue stripping and cleaning composition comprising water, one or more alkaline compounds, one or more corrosion inhibitors, and one or more oxidized products of one or more antioxidants, wherein the one or more oxidized products of one or more antioxidants comprise 0.05 wt % or more of said composition.

2. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claim 1 wherein said one or more corrosion inhibitors comprise one or more antioxidant corrosion inhibitors.

3. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claims 2, wherein said one or more oxidized products of one or more antioxidants are formed by oxidizing said one or more antioxidant corrosion inhibitors.

4. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claim 2, wherein said one or more oxidized products of one or more antioxidants were formed in situ by adding oxygen-containing gas, peroxides or nitrates to said composition.

5. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claim 2, wherein said one or more antioxidant corrosion inhibitors are selected from the group consisting of catechol, t-butyl catechol, resorcinol, pyrogallol, gallic acid, esters of gallic acid and ascorbic acid.

6. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claim 2, further comprising one or more passivation corrosion inhibitors.

7. The photoresist or semiconductor manufacturing residue stripping and cleaning composition of claim 6, wherein said one or more passivation corrosion inhibitors are selected from the group consisting of anthranilic acid, benzoic acid, isophthalic acid, maleic acid, fumaric acid, D,L-malic acid, malonic acid, phthalic acid, maleic anhydride, phthalic anhydride, benzotriazole (BZT), carboxybenzotriazole, diethyl hydroxylamine, lactic acid and citric acid salts thereof, pyrogallol, fructose, ammonium thiosulfate, glycine, lactic acid, tetramethylguanidine, iminodiacetic acid, and